Ka-Band Monolithic GaAs FET Power Amplifier Modules (1988 Vol. I [MWSYM])

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Monolithic GaAs FET power amplifiers consisting of several power combined devices have been fabricated and evaluated. The baseline monolithic chip design consists of a single stage 400µm FET amplifier and a six-way travelling-wave power divider/combiner with a single stage amplifier in each of the six arms. Several chip combinations were used to make a 1 W amplifier with 5 dB gain and a 0.55 W amplifier with 27 dB gain at 34 GHz.

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